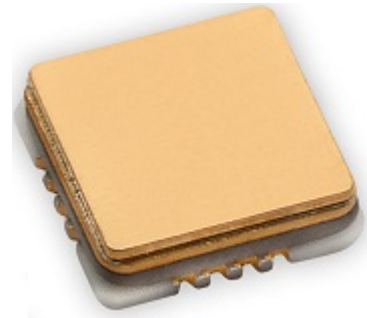


Power amplifier, GPA-4.5-7.5-41-QFN

Parameters

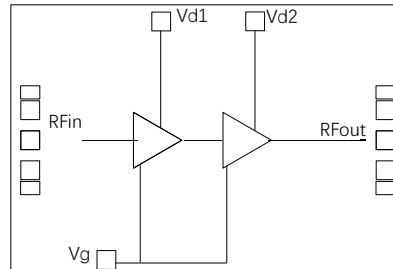
- Operating frequency: 4.5~7.5GHz
- Psat: 41.0dBm
- Power gain: 20dB@Pin=22dBmPower
- supply: 28V/-2.7V
- 50ohm input/output
- Chip size: 5.0mm×5.0mm×1.6mm



Product introduction

GPA-4.5-7.5-41 is a power amplifier chip manufactured using GaN HEMT technology. The working frequency band covers 4.5~7.5 GHz, and under a supply voltage of 28V, it can provide a power gain of 20dB, with a saturated output power greater than 41dBm. The chip is grounded through the back through-hole, mainly used in communication systems, high-power transceiver components, and other fields.

Internal block diagram



Max. operating conditions^[1]

| Parameter | Ratings |
|-----------------------|------------|
| Drain voltage | +30V |
| Input power | 30dBm |
| Operating temperature | -55℃~+85℃ |
| Storage temperature | -65℃~+120℃ |

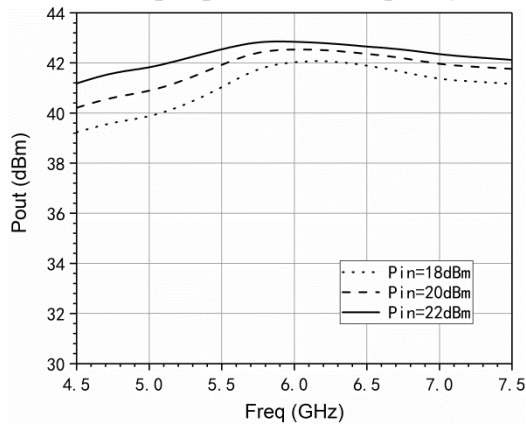
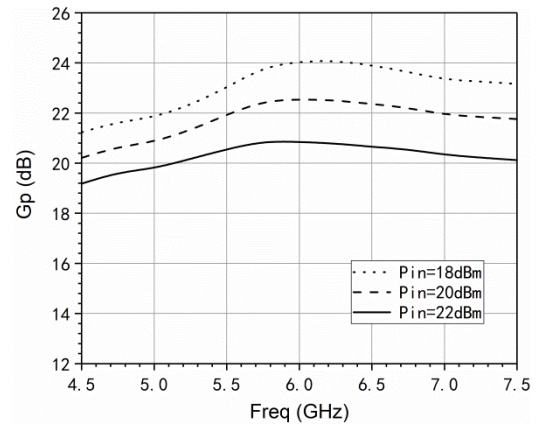
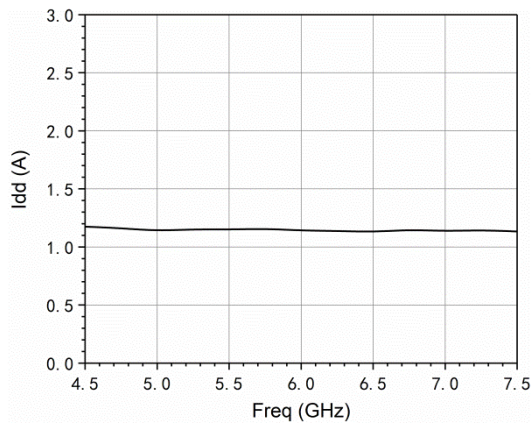
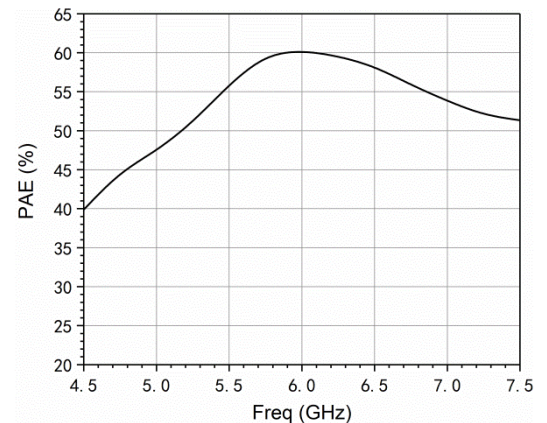
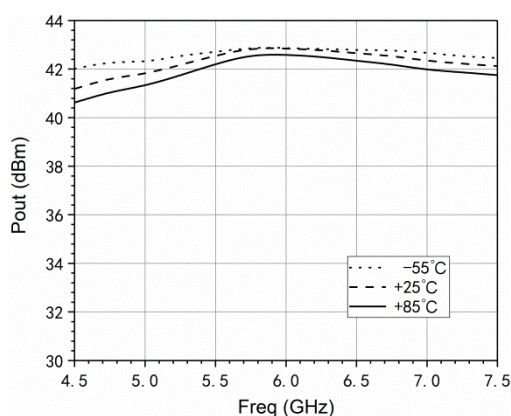
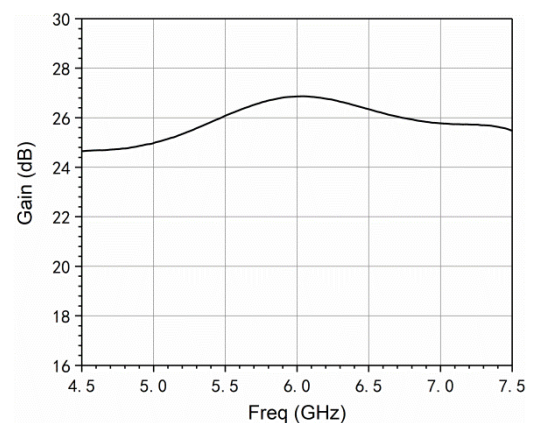
[1] Exceeding any of these limits may cause permanent damage.

DC electrical specifications (TA=+25 °C)

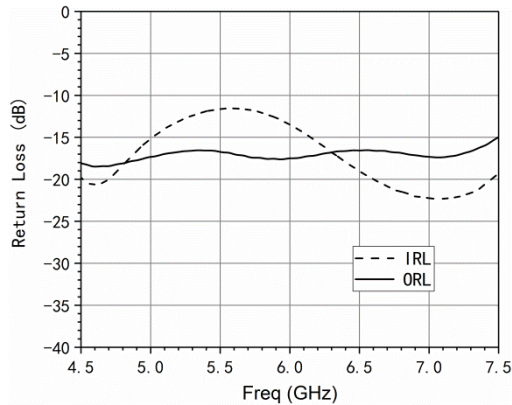
| Parameter | Min | Typ | Max | Unit |
|-------------------------|-----|------|-----|------|
| Gate bias voltage | | -2.7 | | V |
| Drain working voltage | | 28 | | V |
| Quiescent drain current | | 0.55 | | A |
| Dynamic drain current | | 1.2 | | A |

Microwave electrical specifications (TA=+25 °C, Vd=+28V, Vg=-2.7V, CW)

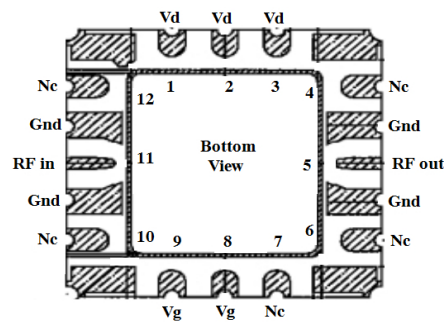
| Parameter | Min | Typ | Max | Unit |
|----------------------------|---------|-------------------------------|-----|------|
| Frequency range | 4.5~7.5 | | | GHz |
| Psat | | 41.0 | | dBm |
| PAE | | 47@5GHz 60@6GHz 54@7GHz | | % |
| Power gain (@Pin=20dBm) | | 20 | | dB |
| Power gain flatness | | ± 0.4 | | dB |
| Input/output return loss | | -11/-16 | | dB |

Typical test results (TA=+25°C, Vd=+28V, Vg=-2.7V, CW)
Output power VS. Frequency

Power gain VS. Frequency

Dynamic current VS. Frequency (@Pin=22dBm)

PAE VS. Frequency (@Pin=22dBm)

Output power VS. Frequency (@Pin=22dBm)

Small signal gain VS. Frequency (@Pin=-25dBm)


Input/output return loss VS. Frequency



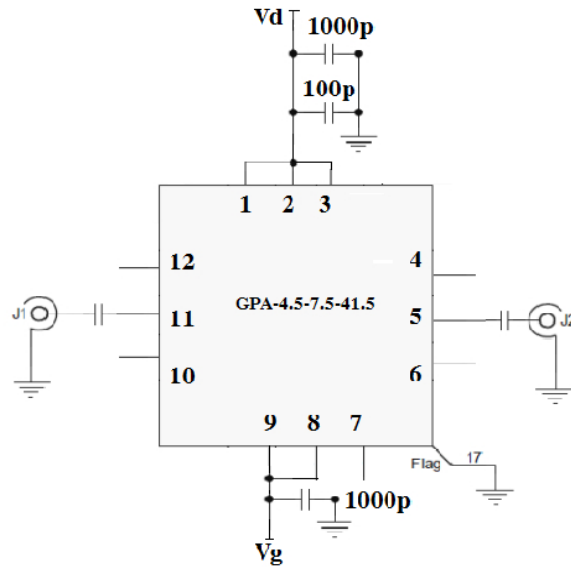
QFN Bottom view diagram



Pad Definition

| Pad Number | Function | Description | Remark |
|------------|----------|--|---------|
| 1、2、3 | Vd | Drain power supply | 28VDC |
| 5 | OUT | RF output, external 50 ohm system, no need for external blocking capacitor | |
| 11 | IN | RF input, external 50 ohm system, no need for external blocking capacitor | |
| 8、9 | Vg | Gate power supply | -2.7VDC |

Application schematic diagram



Note: To ensure more stable performance of the amplifier, it is recommended to weld ceramic capacitors with the recommended capacitance values in the above assembly diagram at the feeding end for filtering. The number of filtering capacitors can also be increased or different capacitance values can be combined according to actual needs.

Note:

1. Please assemble and use in a purified environment, store in anti-static containers, and keep dry
2. This product is an electrostatic sensitive device. Please pay attention to anti-static measures during storage and use
3. Do not attempt to clean the surface of the chip using dry or wet chemical methods
4. If you have any questions, please contact the supplier



This product is sensitive to static electricity. Please pay attention to anti-static measures during use